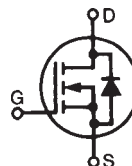


PolarHV™ HiPerFET Power MOSFET

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

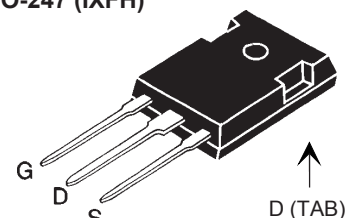
IXFH 26N50P
IXFV 26N50P
IXFV 26N50PS



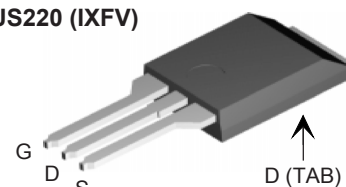
$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 26 \text{ A} \\ R_{DS(on)} &\leq 230 \text{ m}\Omega \\ t_{rr} &\leq 200 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GSS}	Continuos	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	26	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	78	A
I_{AR}	$T_C = 25^\circ\text{C}$	26	A
E_{AR}	$T_C = 25^\circ\text{C}$	40	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
F_C	Mounting force (PLUS220)	11..65/2.5..15	N/lb
Weight	TO-247	6	g
	PLUS220 & PLUS220SMD	5	g

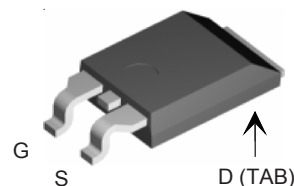
TO-247 (IXFH)



PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 μA
				250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			230 $\text{m}\Omega$

Features

- International standard packages
- Fast intrinsic diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

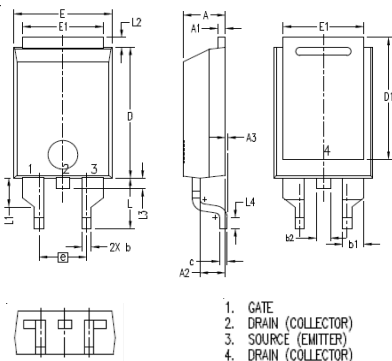
Advantages

- Easy to mount
- Space savings
- High power density

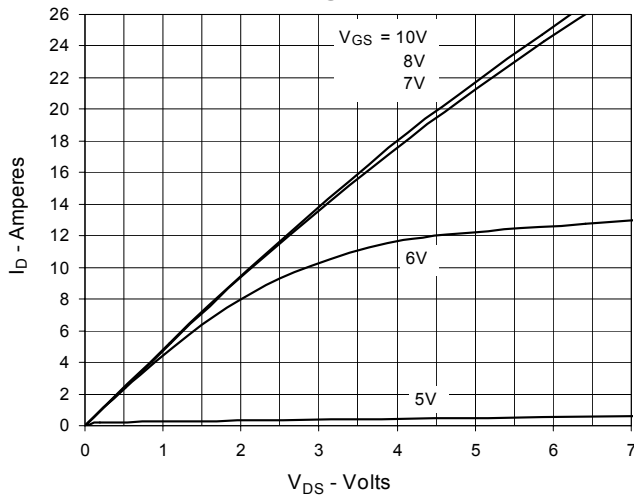
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$, pulse test	16	26	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3600	pF
C_{oss}			370	pF
C_{rss}			40	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 I_{D25}$ $R_G = 4\ \Omega$ (External)		20	ns
t_r			25	ns
$t_{d(off)}$			58	ns
t_f			20	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		60	nC
Q_{gs}			20	nC
Q_{gd}			25	nC
R_{thJC}	(TO-247, PLUS220)		0.21	0.31°C/W
R_{thCS}				$^\circ\text{C/W}$

Source-Drain Diode

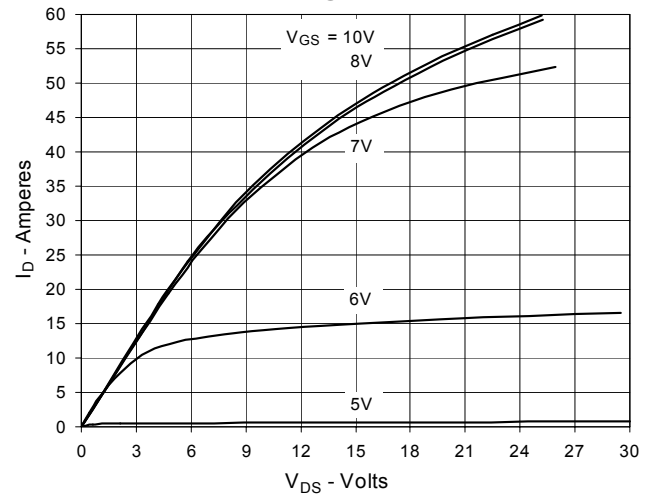
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			26 A
I_{SM}	Repetitive			104 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}, V_{GS} = 0\text{ V}$		0.6	200 ns
Q_{RM}				μC
I_{RM}				A

PLUS220SMD (IXFV_S) Outline


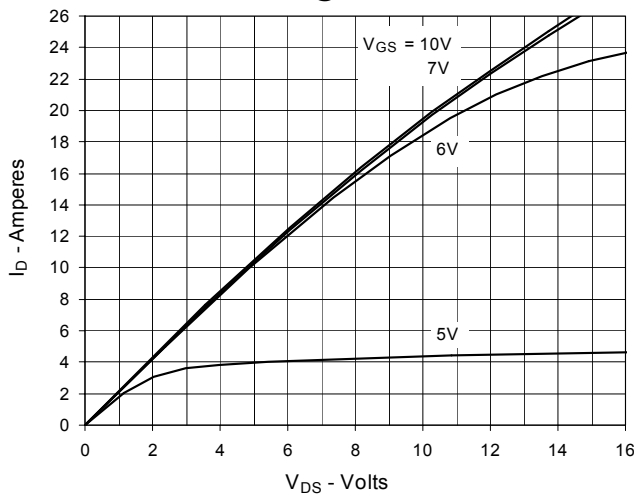
**Fig. 1. Output Characteristics
@ 25°C**



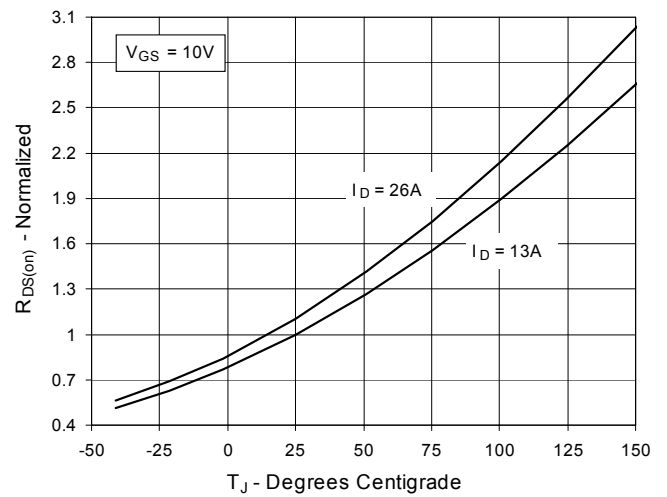
**Fig. 2. Extended Output Characteristics
@ 25°C**



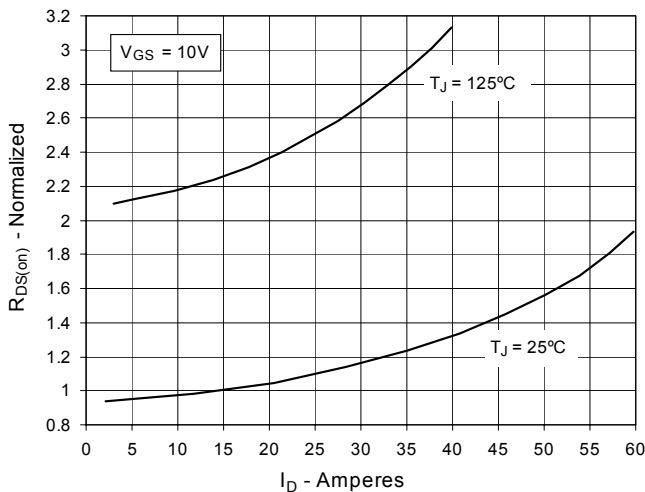
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 13A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 13A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

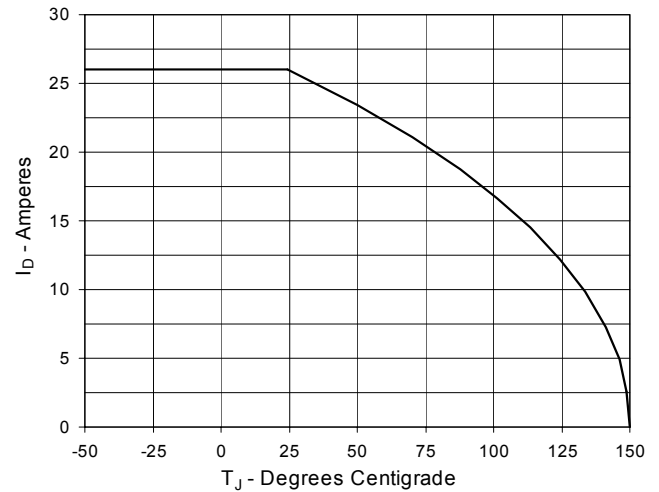


Fig. 7. Input Admittance

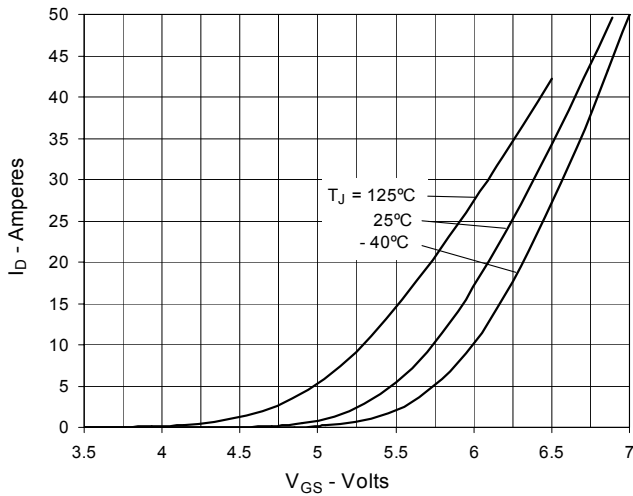


Fig. 8. Transconductance

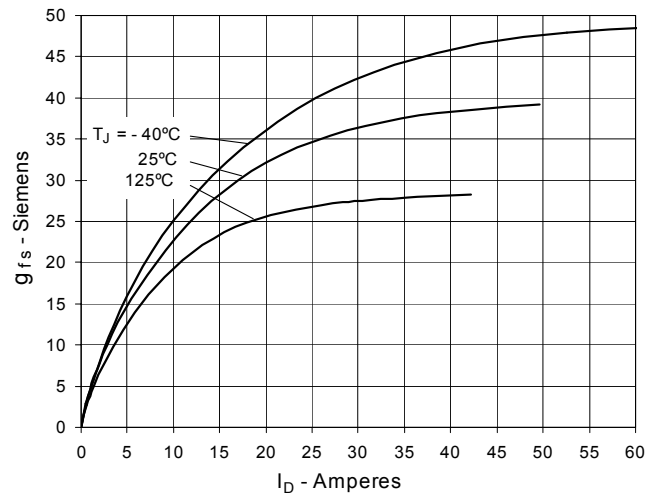


Fig. 9. Forward Voltage Drop of Intrinsic Diode

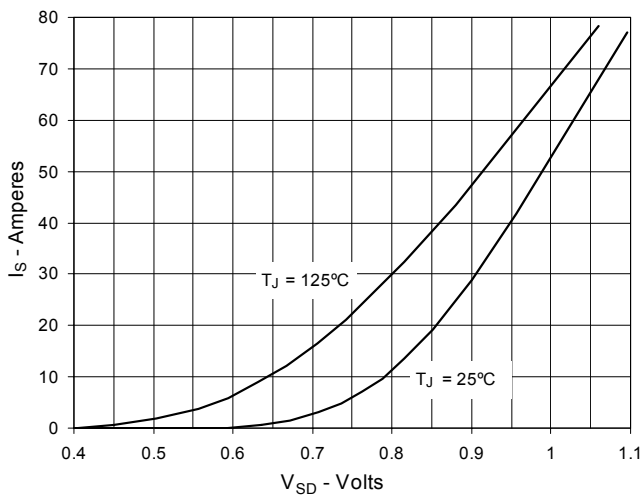


Fig. 10. Gate Charge

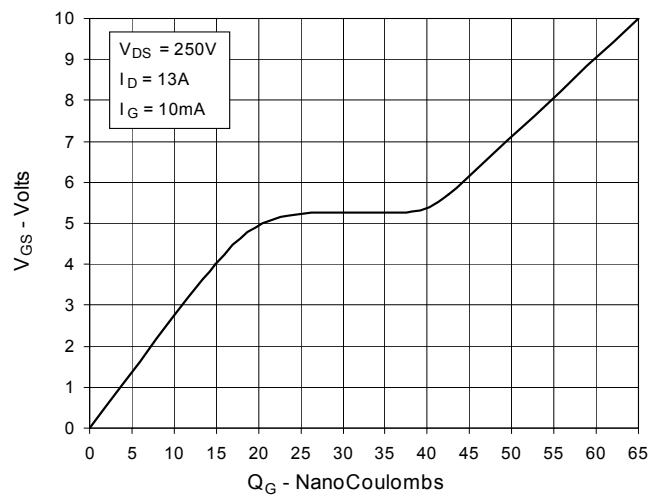


Fig. 11. Capacitance

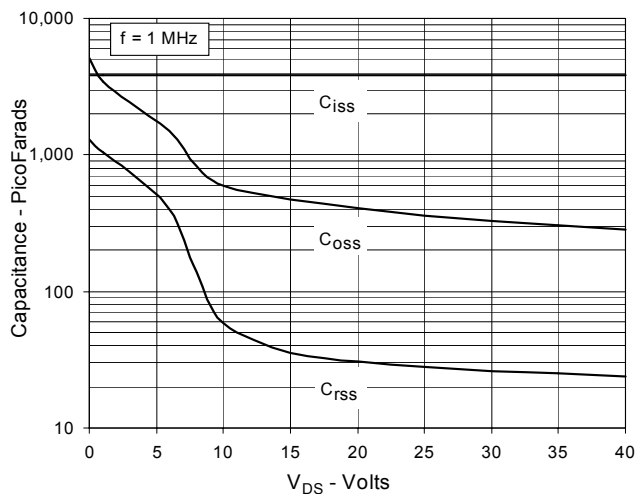


Fig. 12. Forward-Bias Safe Operating Area

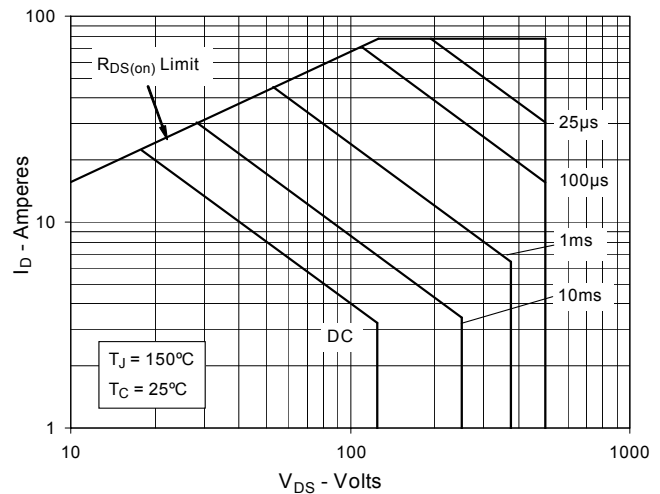
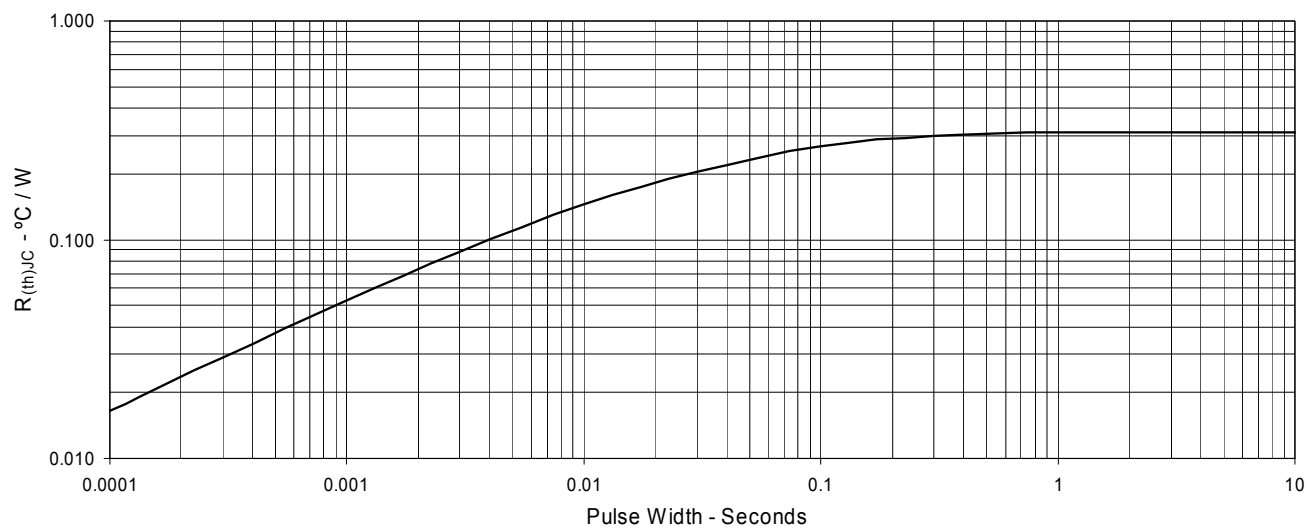


Fig. 13. Maximum Transient Thermal Resistance



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